AMENDMENT TO THE CLAIMS:

Please amend the claims as follows. Strikethroughs indicate deletions and underlines indicate additions.

Claim 1 (Currently Amended): Complaint substrate (5, 20, 30) comprising a carrier (1, 14, 21, 31) and at least one thin layer (4, 13, 23, 34) formed on the surface of said carrier and intended to be used as a seed for a hetero-epitaxial growth ~~receive, in integral manner, a stress-giving structure~~, the carrier and the thin layer being joined one to another by joining means (3~~,~~ 11, 15, 16~~,~~ 24, 25) such that the stresses brought by said structure are absorbed in whole or in part by the thin layer and/or the joining means, ~~characterized in that~~ wherein said joining means ~~comprise at least one joining zone chosen from among the following joining zones~~ is selected from the group consisting of: a layer of microcavities, and ~~/or~~ a bonding interface whose bonding energy is controlled to permit the absorption of said stresses.

Claim 13 (Currently Amended): Compliant substrate according to claim 1, characterized in that said bonding interface with controlled bonding energy is an interface resulting from a ~~controlled by~~ surface preparation and/or an interface resulting from a heat treatment and/or an interface resulting from a creation of defects ~~at this interface~~.

Claim 14 (Currently Amended): Compliant substrate according to claim 13, characterized in that surface preparation is a control of roughness and/or hydrophili~~a~~c.

Claim 15 (Currently Amended): Compliant substrate according to Claim 13, characterized in that said joining zone also comprises at least one intermediate layer (22, 32, 33) between the thin layer (23, 34) and the carrier (21, 31).

Claim 16 (Currently Amended): Compliant substrate according to claim 15, characterized in that the intermediate layer (22, 32, 33) is a metal layer or metal alloy layer.

Claim 17 (Currently Amended): Compliant substrate according to claim 15, characterized in that at least one intermediate layer is formed such that it comprises ~~is made up of~~ non-homogeneities able to relax stresses.

Claim 18 (Cancelled)

Claim 19 (Previously Amended): Compliant substrate (5, 20, 30) according to Claim 1, characterized in that said thin layer (4, 13, 23, 34) is in a first crystalline material and is intended to be used as hetero-epitaxial growth seed for a second crystalline material forming said structure.

Claim 20 (Currently Amended): Compliant substrate according to claim 19, characterized in that said thin layer is a pre-stressed layer ~~through the insertion~~by the presence of a foreign element in said first crystalline material in order to promote the compliance of said substrate.

Claim 21 (Original): Compliant substrate according to claim 20, characterized in that the foreign element is inserted through implantation by bombardment and/or inserted by diffusion.

Claim 22 (Previously Amended): Compliant substrate according to Claim 20, characterized in that said foreign element is a doping agent of the thin layer.

Claim 23 (Previously Amended): Compliant substrate (5, 20, 30) according to Claim 19, characterised in that said first crystalline material is a semiconductor.

Claim 24 (Previously Amended): Application of the compliant substrate (5, 20, 30) according to Claim 19, to the hetero-epitaxial growth of a crystalline material chosen from among GaN, SiGe, A1N, InN, and SiC.

Claim 29 (Previously Added): Compliant substrate according to Claim 14, characterized in that said joining zone also comprises at least one intermediate layer (22; 32, 33) between the thin layer (23; 34) and the carrier (21; 31).

Claim 30 (Cancelled)

Claim 31 (Previously Added): Compliant substrate (5, 20, 30) according to Claim 18, characterized in that said thin layer (4, 13, 23, 34) is in a first crystalline material and

is intended to be used as hetero-epitaxial growth seed for a second crystalline material forming said structure.

Claim 32 (Previously Added): Compliant substrate according to Claim 21, characterized in that said foreign element is a doping agent of the thin layer.

Claim 33 (Previously Added): Compliant substrate (5, 20, 30) according to Claim 22, characterized in that said first crystalline material is a semiconductor.

Claim 34 (Previously Added): Application of the compliant substrate (5, 20, 30) according to Claim 23, to the hetero-epitaxial growth of a crystalline material chosen from among GaN, SiGe, A1N, InN and SiC.